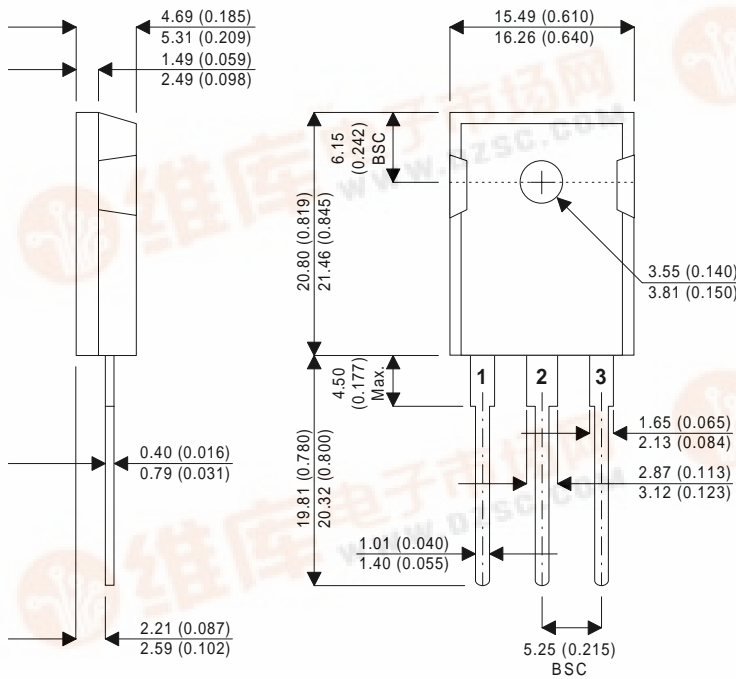


BUZ905P
BUZ906P

MECHANICAL DATA

Dimensions in mm (inches)



TO-247

Pin 1 – Gate

Pin 2 – Source

Pin 3 – Drain

**P-CHANNEL
POWER MOSFET**

**POWER MOSFETS FOR
AUDIO APPLICATIONS**

FEATURES

- HIGH SPEED SWITCHING
- P-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- N-CHANNEL ALSO AVAILABLE AS BUZ900P & BUZ901P

ABSOLUTE MAXIMUM RATINGS

(T_{case} = 25°C unless otherwise stated)

		BUZ905P	BUZ906P
V _{DSX}	Drain – Source Voltage	-160V	-200V
V _{GS}	Gate – Source Voltage	±14V	
I _D	Continuous Drain Current	-8A	
I _{D(PK)}	Body Drain Diode	-8A	
P _D	Total Power Dissipation @ T _{case} = 25°C	125W	
T _{stg}	Storage Temperature Range	-55 to 150°C	
T _j	Maximum Operating Junction Temperature	150°C	
R _{θJC}	Thermal Resistance Junction – Case	1.0°C/W	





BUZ905P
BUZ906P

STATIC CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX}	Drain – Source Breakdown Voltage	V _{GS} = 10V	BUZ905P	-160			V
		I _D = -10mA	BUZ906P	-200			
BV _{GSS}	Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100μA	±14			V
V _{GS(OFF)}	Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.15		-1.5	V
V _{DS(SAT)} *	Drain – Source Saturation Voltage	V _{GD} = 0	I _D = -8A			-12	V
I _{DSX}	Drain – Source Cut-Off Current	V _{GS} = -10V	V _{DS} = -160V			-10	mA
			BUZ905P				
			V _{DS} = -200V			-10	
			BUZ906P				
yfs*	Forward Transfer Admittance	V _{DS} = -10V	I _D = -3A	0.7		2	S

DYNAMIC CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
C _{iss}	Input Capacitance	V _{DS} = 10V f = 1MHz			734		pF
C _{oss}	Output Capacitance				300		
C _{rss}	Reverse Transfer Capacitance				26		
t _{on}	Turn-on Time	V _{DS} = -20V			120		ns
t _{off}	Turn-off Time	I _D = -5A			60		

* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

